N-Channel Enhancement Mode Field Effect Transistor

Product Summary

● V_{DS}	40V
● I_D	155A
● $R_{DS(ON)}$(at V_{GS}=10V)	2.5mohm
● 100% EAS Tested	
● 100% VDS Tested	

General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- U

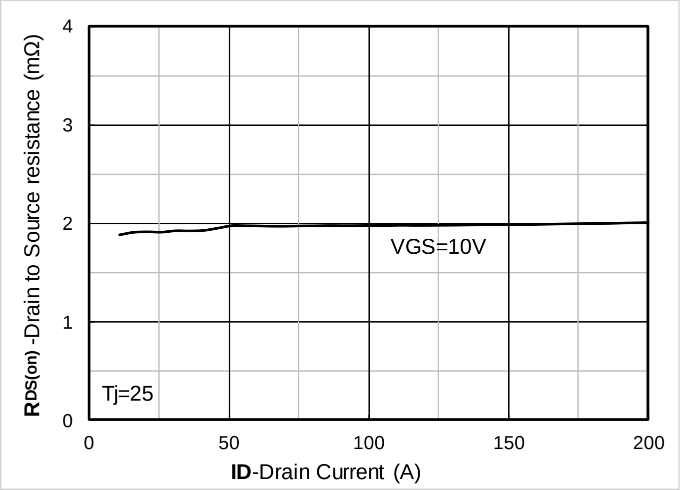

Figure7. RDS(on) VS Drain Current

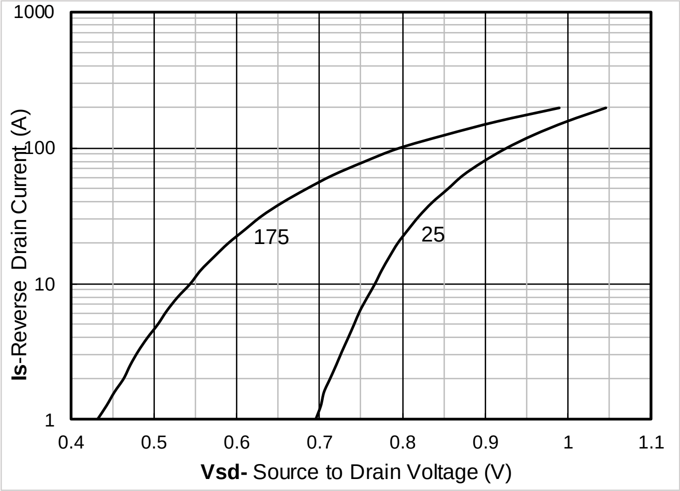

Figure8. Forward characteristics of reverse diode

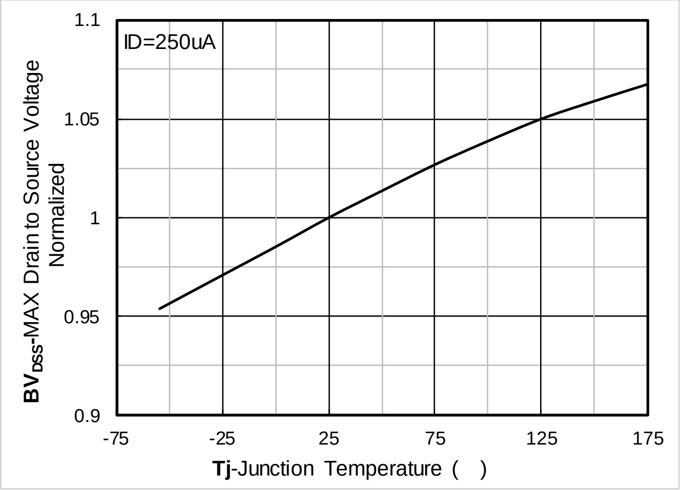

Figure9. Normalized breakdown voltage

Figure10. Normalized Threshold voltage

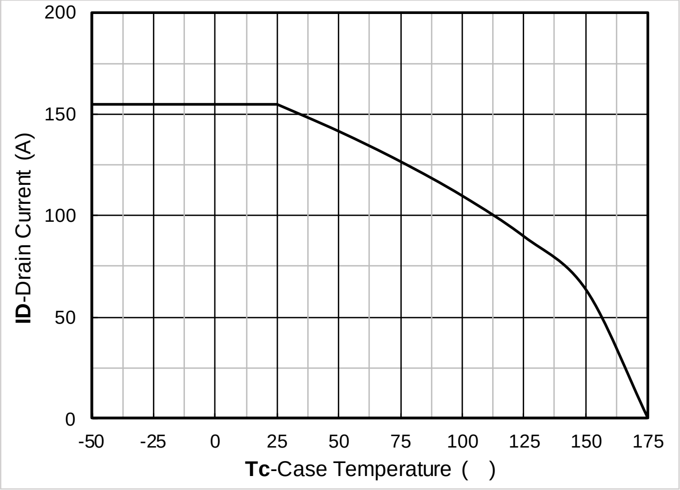

Figure11. Current dissipation

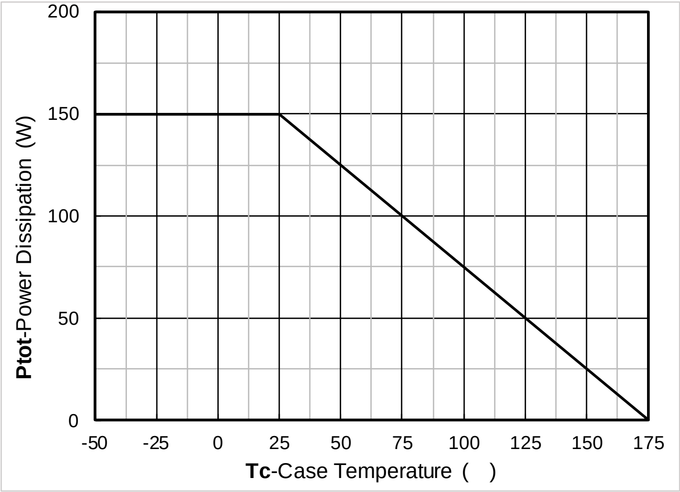

Figure12. Power dissipation

■ TO-263-HY Package information

SYM.	MIN.	
A2		
b2		0.050
c		
c2		
D2		
E		
E1		

Disclaimer

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